

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:

K. YOSHIOKA, et al.

Serial No.:

10/083,353

Filed:

February 27, 2002

For:

APPARATUS FOR PROCESSING SPECIMENS

Group:

1763

Examiner:

K. Moore

AMENDMENT

Commissioner for Patents Washington, D.C. 20231

February 3, 2003

Sir:

In response to the Office Action mailed October 1, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend Claims 1 - 3 as follows:

1. (Amended) An apparatus for processing a specimen having two or more layers, at least one of which includes NiFe or NiFeCo alloy and which is laminated on a substrate, comprising:

an etching process unit, which is supplied with a gas that produces a high density gas plasma of a low ion energy with the gas and performs etching of the specimen laminated on the substrate, with the produced high density plasma gas under a temperature of the specimen below 200°C;

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